

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
30V	18mΩ @ V _{GS} = 10V	8.6A
	27mΩ @ V _{GS} = 4.5V	5.5A

Description

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

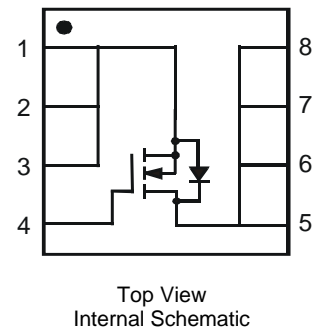
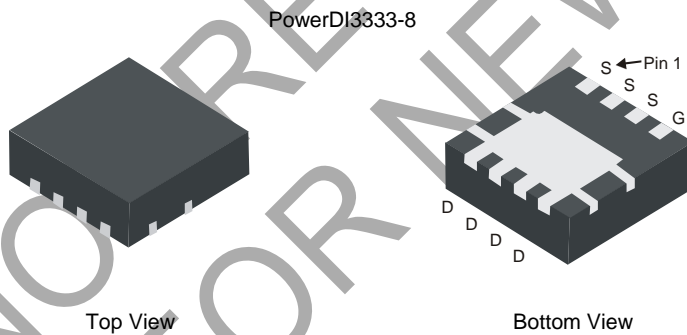
- Backlighting
- DC-DC converters
- Power management functions

Features

- Low R_{DS(ON)} – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.072 grams (Approximate)

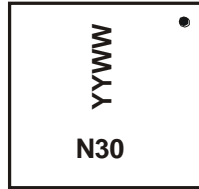


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN3030LFG-7	PowerDI3333-8	2000	Tape & Reel
DMN3030LFG-13	PowerDI3333-8	3000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



N30 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 22 for 2022)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.3 4.2	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	6.8 5.2	A
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	8.6 6.8	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	11 8.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	70	A
Maximum Body Diode Continuous Current			I _S	3	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.9	W
	T _A = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	148	°C/W
	t < 10s		89	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.3	W
	T _A = +70°C		1.4	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	56	°C/W
	t < 10s		34	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	6.9	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	100	nA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±1	μA	V _{GS} = ±25V, V _{DS} = 0V
		—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.8	1.2	2.1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	10	18	mΩ	V _{GS} = 10V, I _D = 10A
		—	16	27		V _{GS} = 4.5V, I _D = 7.5A
Forward Transfer Admittance	Y _{fs}	—	6	—	S	V _{DS} = 5V, I _D = 10A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	751	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	121	—		
Reverse Transfer Capacitance	C _{rss}	—	110	—		
Gate Resistance	R _g	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge V _{GS} = 4.5V	Q _g	—	9	—	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 6A
Total Gate Charge V _{GS} = 10V	Q _g	—	17.4	—		
Gate-Source Charge	Q _{gs}	—	2.2	—		
Gate-Drain Charge	Q _{gd}	—	3	—		
Turn-On Delay Time	t _{D(ON)}	—	2.5	—	ns	V _{DD} = 15V, V _{GS} = 10V R _G = 6Ω, R _L = 1.8Ω, I _D = 6.7A
Turn-On Rise Time	t _r	—	6.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	19.0	—		
Turn-Off Fall Time	t _f	—	6.3	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

NOT RECOMMENDED FOR NEW DESIGN

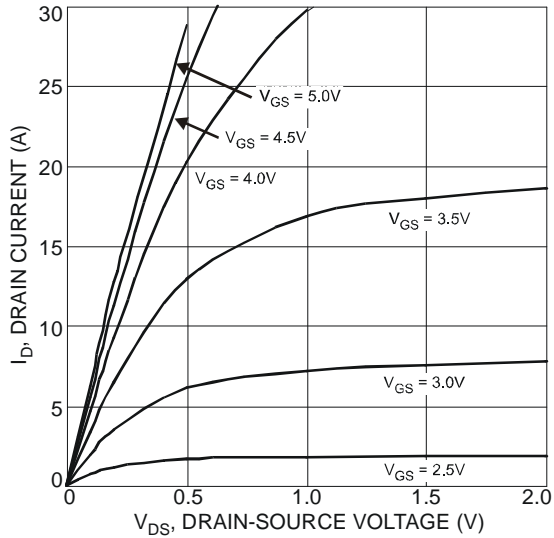


Fig. 1 Typical Output Characteristic

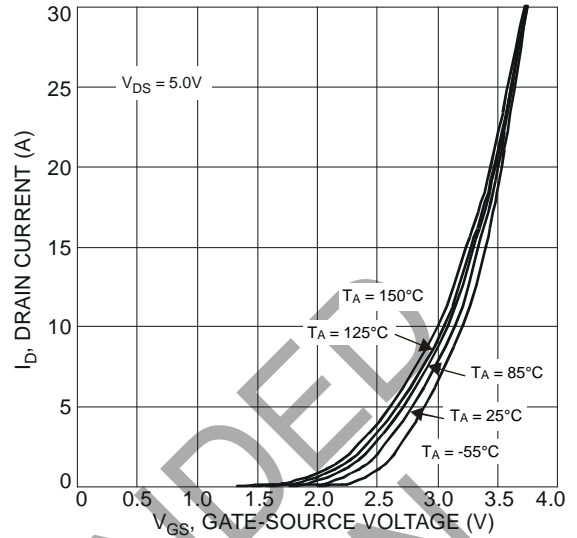


Fig. 2 Typical Transfer Characteristics

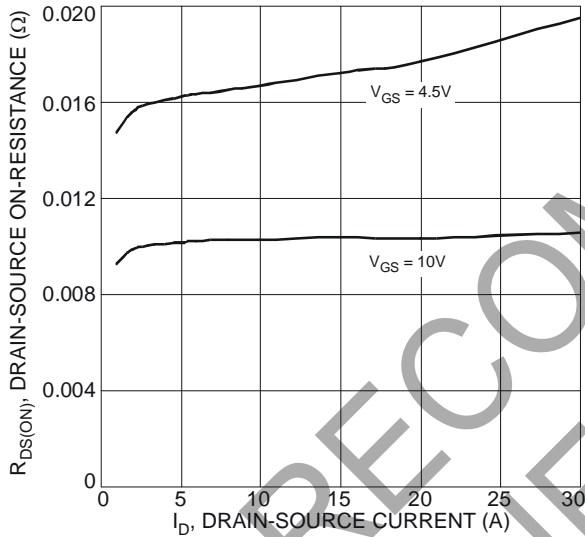


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

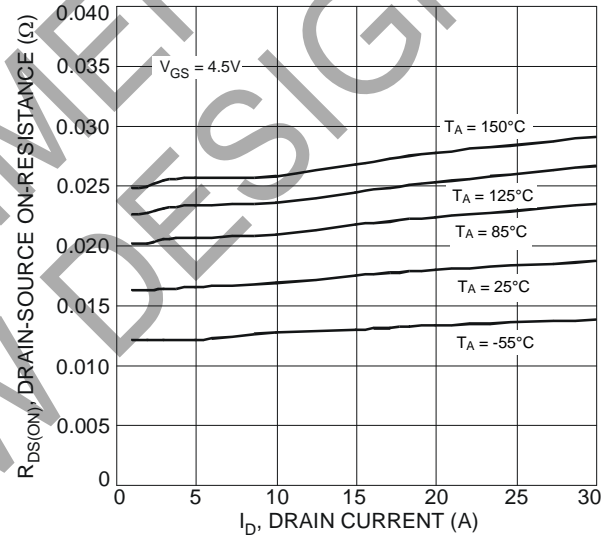


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

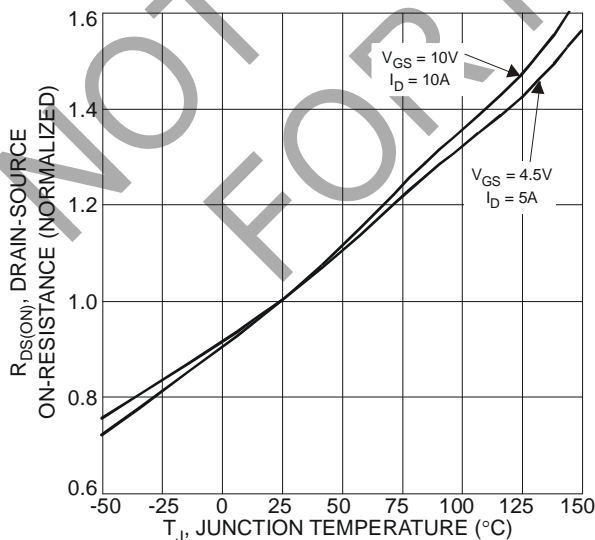


Fig. 5 On-Resistance Variation with Temperature

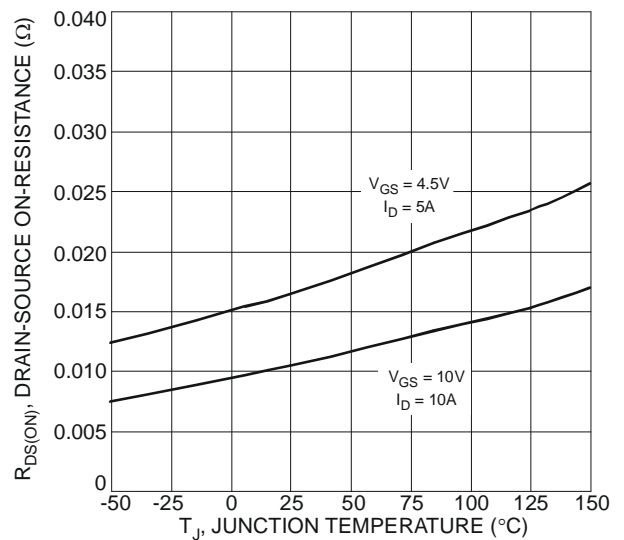


Fig. 6 On-Resistance Variation with Temperature

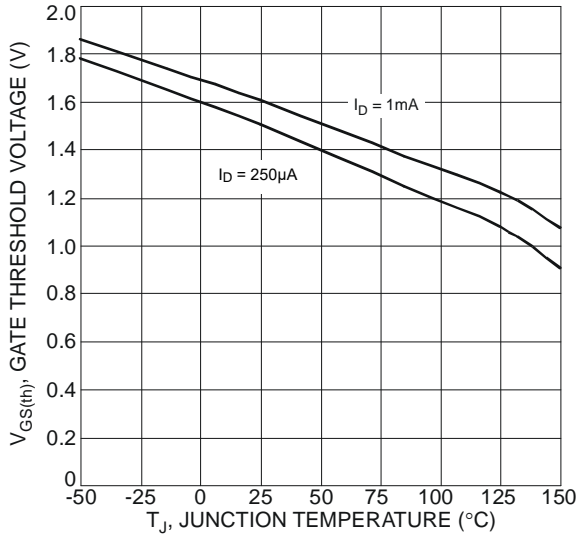


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

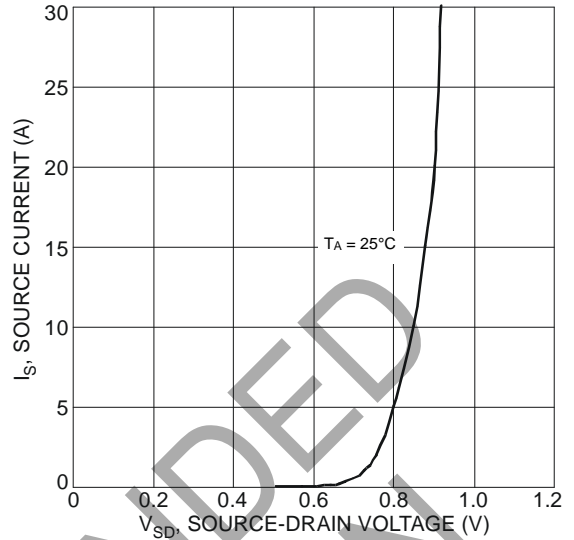


Fig. 8 Diode Forward Voltage vs. Current

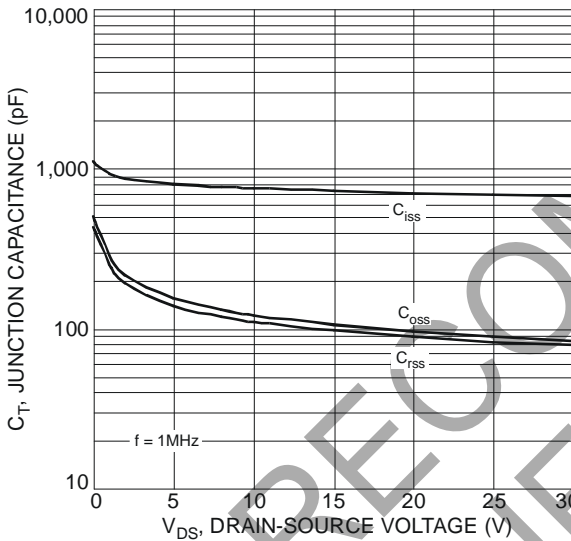


Fig. 9 Typical Junction Capacitance

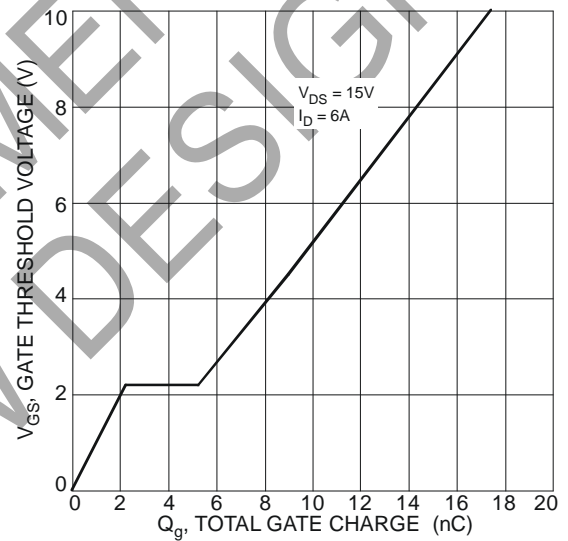


Fig. 10 Gate Charge

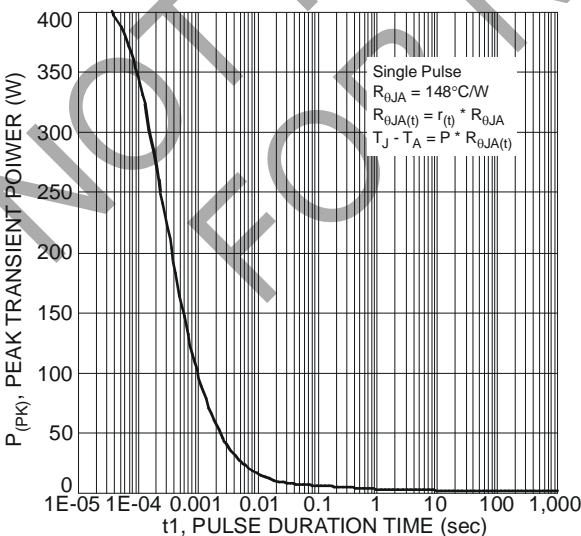


Fig. 11 Single Pulse Maximum Power Dissipation

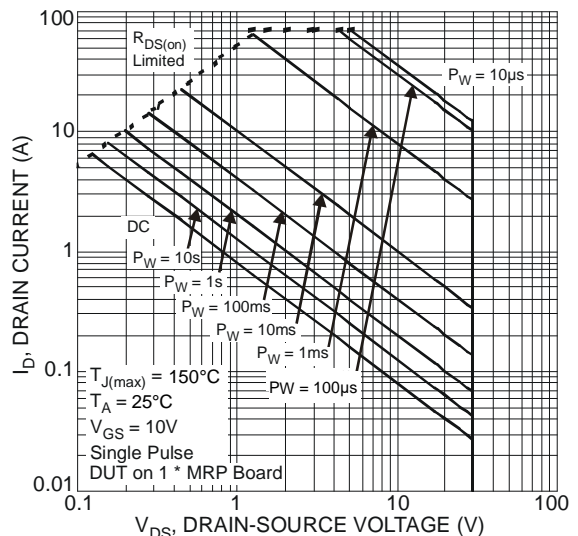


Fig. 12 SOA, Safe Operation Area

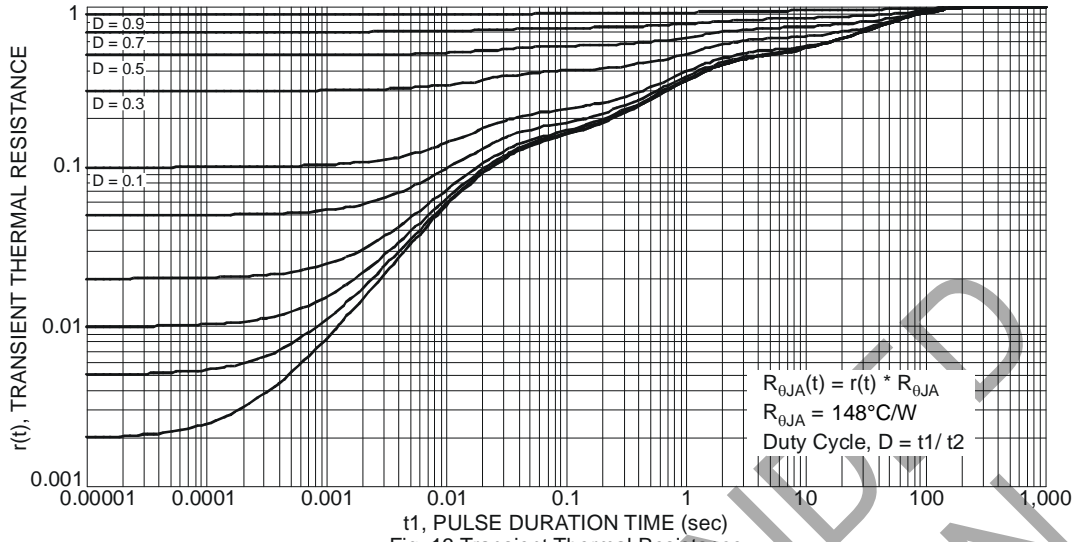


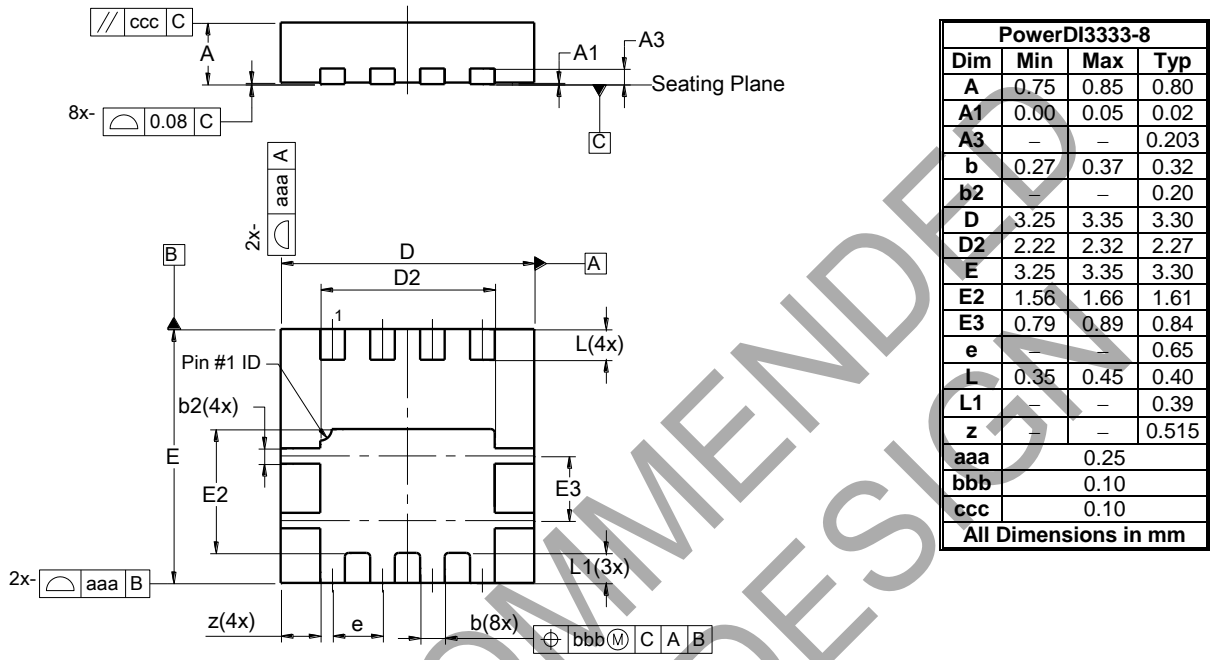
Fig. 13 Transient Thermal Resistance

NOT RECOMMENDED FOR NEW DESIGN

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

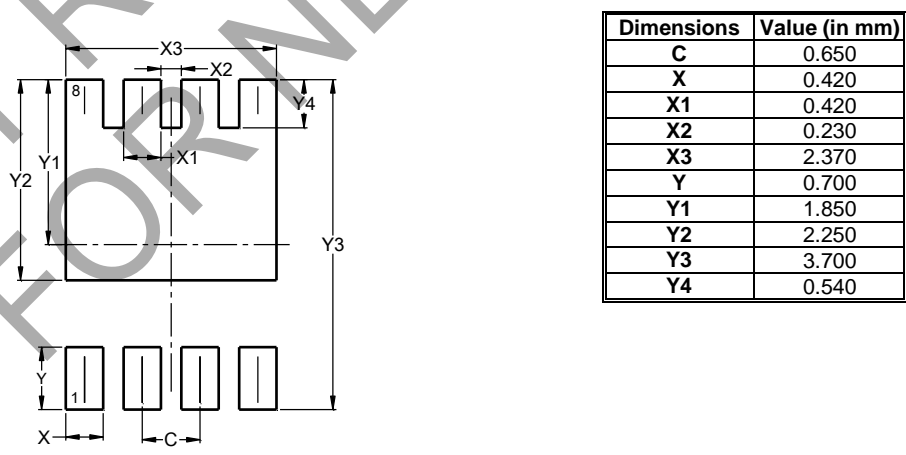
PowerDI3333-8



Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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